

Supporting Information

Solution-Processed Amorphous ZrO₂ Gate Dielectric Films

Synthesized by a Non-Hydrolytic Sol-Gel Route

Jong-Baek Seon,^a Nam-Kwang Cho,^a Gayeong Yoo,^a Youn Sang Kim^{*ab} and Kookheon Char^{*c}

^a*Program in Nano Science and Technology, Graduate School of Convergence Science and Technology, Seoul National University, Seoul 151-744, Republic of Korea. Tel: +82-31-888-9143; E-mail: younskim@snu.ac.kr.*

^b*Advanced Institutes of Convergence Technology, 864-1 Iui-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do 443-270, Republic of Korea.*

^c*School of Chemical and Biological Engineering, Seoul National University, Seoul 08826, Republic of Korea. E-mail: khchar.snu.ac.kr*

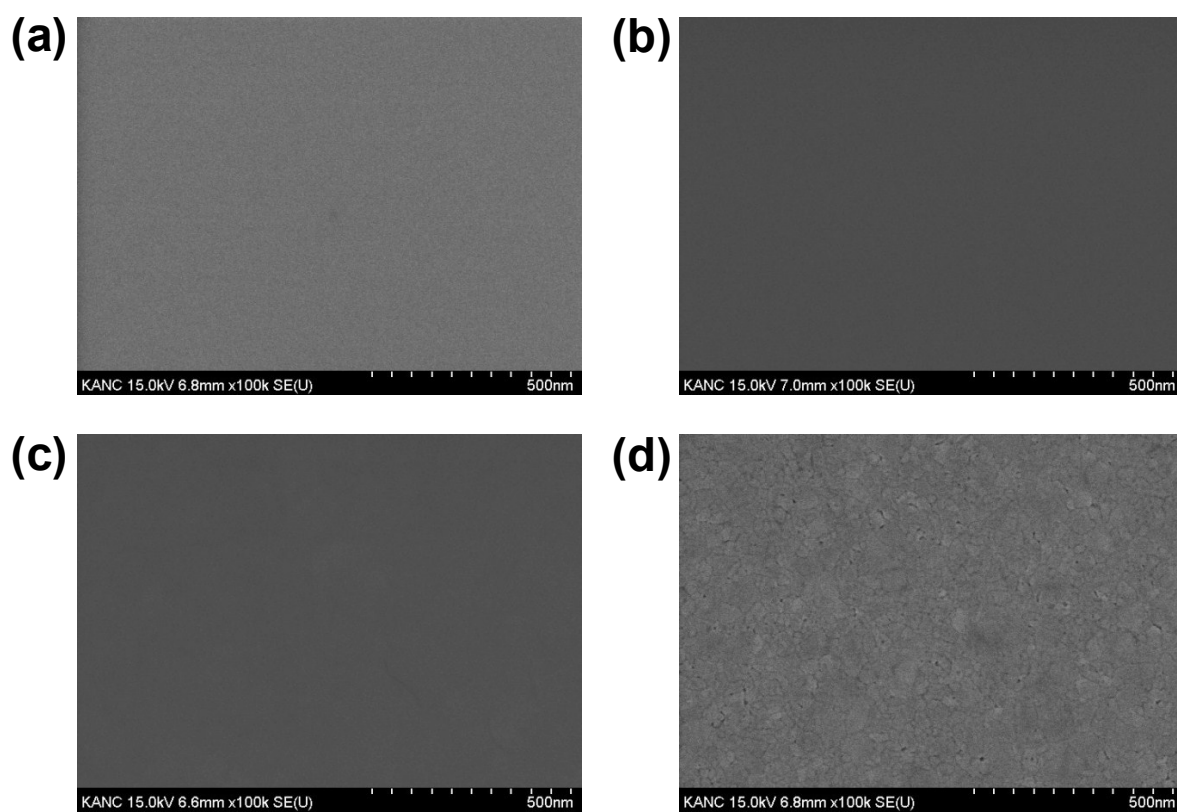


Fig. S1. SEM images of (a) thermally oxidized thin SiO₂ films (reference), spin-coated thin ZrO₂ films post-annealed at (a) 300 °C, (b) 400 °C, and (c) 600 °C, respectively.